

**Listing of Claims:**

1. (Currently Amended) A semiconductor device comprising:  
a semiconductor substrate including a circuit  
element-forming region in which an integrated circuit is formed,  
and a plurality of connection pads;

5 an organic insulating film formed on said circuit element-forming region;

a plurality of columnar electrodes which ~~are provided~~ each  
have an upper edge surface outwardly exposed for connection to  
an external terminals device, and which are each electrically  
10 connected to at least one of said plurality of connection pads;

at least one thin film passive element including at least  
one conductive layer formed on said insulating film; and

a sealing film which is provided between the columnar  
electrodes, and which covers the ~~at least one~~ thin film passive  
15 element [[,]] and ~~from which an~~ the semiconductor substrate  
except for the upper edge surface of each of the columnar  
electrodes ~~is exposed~~.

2. (Previously Presented) The semiconductor device according  
to claim 1, wherein said thin film passive element comprises at  
least one capacitance element.

3. (Previously Presented) The semiconductor device according to claim 2, wherein:

said capacitance element includes two conductive layers and a dielectric material layer,

5 said two conductive layers are stacked one upon the other on said insulating film, and

said dielectric material layer is interposed between the conductive layers.

4. (Currently Amended) The semiconductor device according to claim 2, wherein:

said at least one conductive layer of said capacitance element includes at least two portions having opposing end surfaces and formed in one layer on said insulating film, and

5 a dielectric material layer is formed in a clearance between the opposing end surfaces of the at least two portions.

5. (Currently Amended) The semiconductor device according to claim 2, wherein:

said at least one conductive layer of said capacitance element includes at least two portions having opposing end surfaces and formed in one layer on said insulating film,

5 said columnar electrodes are formed as plate-like electrodes respectively positioned on the at least two portions, and

a dielectric material layer is formed at least in a clearance between the opposing end surfaces of the plate-like electrodes.

6. (Previously Presented) The semiconductor device according to claim 1, wherein said thin film passive element comprises at least one inductance element.

7. (Previously Presented) The semiconductor device according to claim 6, wherein:

said inductance element includes one conductive layer having one of an angular eddy shape, a rectangular wave shape, and a loop shape,

said connection pads include at least one first connection pad that is not electrically connected to any of said columnar electrodes, and at least one second connection pad electrically connected to at least one of said columnar electrodes, and

said inductance element includes at least two terminals, at least one of which is connected to at least one of said first connection pad and said second connection pad.

8. (Previously Presented) The semiconductor device according to claim 7, wherein said inductance element further comprises a magnetic film formed on said one conductive layer.

9. (Previously Presented) The semiconductor device according to claim 1, wherein said thin film passive element includes at least two terminals, at least one of which is electrically connected to one of said columnar electrodes.

10. (Previously Presented) The semiconductor device according to claim 1, wherein said thin film passive element includes at least two terminals, at least one of which is electrically connected to one of said connection pads.

11. (Previously Presented) The semiconductor device according to claim 1, wherein said thin film passive element includes at least two terminals, each of which is electrically connected to at least one of said connection pads and said  
5 columnar electrodes.

Claim 12 (canceled)

13. (Currently Amended) The semiconductor device according to claim 1, wherein said at least one thin film passive element comprises a plurality of thin film passive elements.

14. (Currently Amended) A method of manufacturing a semiconductor device comprising:

preparing a semiconductor wafer substrate including a plurality of chip forming regions each having a circuit element-forming region in which an integrated circuit is formed,  
5 and a plurality of connection pads;

forming an organic insulating film on the circuit element-forming region of each of said chip forming regions;

forming a plurality of columnar electrodes which are  
10 provided for connection to an external ~~terminals~~ device, and which are each electrically connected to at least one of said plurality of connection pads;

forming a plurality of thin film passive elements each including at least one conductive layer on said insulating film;

15 forming a sealing film on an exposed entire upper surface of the semiconductor wafer substrate between the columnar electrodes and covering the thin film passive elements and the columnar electrodes;

exposing only an upper edge surface of each of the columnar  
20 electrodes from the sealing film; and

dividing said semiconductor wafer substrate into individual chip forming regions so as to form a plurality of semiconductor devices each having at least one of said thin film passive elements.

15. (Previously Presented) The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive elements comprises forming at least one capacitance element.

16. (Previously Presented) The method of manufacturing a semiconductor device according to claim 15, wherein said forming of each said capacitance element comprises:

forming a first conductive layer on the circuit  
5 element-forming region of said semiconductor substrate;  
forming a dielectric material layer on said first conductive layer; and  
forming a second conductive layer on said dielectric material layer.

17. (Currently Amended) The method of manufacturing a semiconductor device according to claim 15, wherein said forming of each said capacitance element comprises:

forming on said insulating film one conductive layer having  
5 at least two portions having opposing end surfaces; and  
forming a dielectric material layer in a clearance between the opposing end surfaces of the at least two portions.

18. (Currently Amended) The method of manufacturing a semiconductor device according to claim 15, wherein said forming of each said capacitance element comprises:

forming on said insulating film one conductive layer having  
5 at least two portions having opposing end surfaces;

forming said columnar electrodes as plate-like electrodes  
which are opposed to each other respectively on the at least ~~two~~  
two portions; and

forming a dielectric material layer in a clearance between  
10 ~~surfaces of~~ said opposed plate-like electrodes.

19. (Previously Presented) The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive elements comprises forming at least one inductance element.

20. (Previously Presented) The method of manufacturing a semiconductor device according to claim 19, wherein said forming of each said inductance element comprises:

patterning one conductive layer in any one of an angular  
5 eddy shape, a rectangular wave shape and a loop shape;

forming said connection pads to include at least one first connection pad that is not electrically connected to any of said columnar electrodes, and at least one second connection pad

electrically connected to at least one of said columnar

10 electrodes, and

forming at least two terminals, at least one of which is  
connected to at least one of said first connection pad and said  
second connection pad.

21. (Previously Presented) The method of manufacturing a  
semiconductor device according to claim 20, wherein said forming  
of the inductance element further comprises forming a magnetic  
film on said one conductive layer.

Claim 22 (canceled)

23. (Previously Presented) The method of manufacturing a  
semiconductor device according to claim 14, wherein said forming  
of said thin film passive elements comprises forming at least two  
5 terminals, at least one of which is electrically connected to one  
of said columnar electrodes.

24. (Previously Presented) The method of manufacturing a  
semiconductor device according to claim 14, wherein said forming  
of said thin film passive elements comprises forming at least two  
terminals, at least one of which is electrically connected to one  
5 of said connection pads.



25. (Previously Presented) The method of manufacturing a semiconductor device according to claim 14, wherein said forming of said thin film passive elements comprises forming at least two terminals, each of which is electrically connected to at least one of said connection pads and said columnar electrodes.

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